General Purpose Transistor

NPN Silicon

Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	25	Vdc
Collector-Base Voltage	V _{CBO}	30	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	I _C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T _A = 25°C Derate above 25°C	P _D	225 1.8	W mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) @T _A = 25°C Derate above 25°C	P _D	300 2.4	W mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

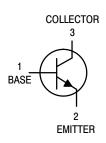
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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MARKING DIAGRAM

STYLE 6



ZC = Device Code

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary
depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT4124LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•	•	
Collector – Emitter Breakdown Voltage (Note 3) (I _C = 1.0 mAdc, I _E = 0)	V _(BR) CEO	25	_	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	V _(BR) CBO	30	_	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	5.0	_	Vdc
Collector Cutoff Current (V _{CB} = 20 Vdc, I _E = 0)	I _{CBO}	-	50	nAdc
Emitter Cutoff Current $(V_{EB} = 3.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	-	50	nAdc
ON CHARACTERISTICS	<u> </u>			
DC Current Gain (Note 3) $ (I_C = 2.0 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) $ $ (I_C = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) $	h _{FE}	120 60	360 -	-
Collector – Emitter Saturation Voltage (Note 3) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{CE(sat)}	-	0.3	Vdc
Base – Emitter Saturation Voltage (Note 3) $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V _{BE(sat)}	-	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS	-			
Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	f _T	300	_	MHz
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	8.0	pF
Collector–Base Capacitance (I _E = 0, V _{CB} = 5.0 V, f = 1.0 MHz)	C _{cb}	-	4.0	pF
Small–Signal Current Gain (I _C = 2.0 mAdc, V_{CE} = 10 Vdc, R_S = 10 k Ω , f = 1.0 kHz)	h _{fe}	120	480	-
Current Gain – High Frequency (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz) (I_C = 2.0 mAdc, V_{CE} = 10 V, f = 1.0 kHz)	h _{fe}	3.0 120	_ 480	-
Noise Figure (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	NF	-	5.0	dB

^{3.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle = 2.0%.

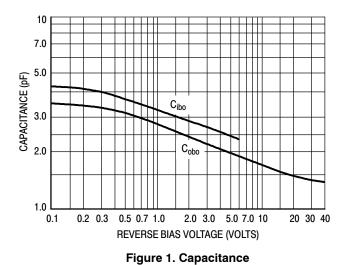


Figure 2. Switching Times

200

AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 $(V_{CE} = 5 \text{ Vdc}, T_A = 25^{\circ}C)$ Bandwidth = 1.0 Hz

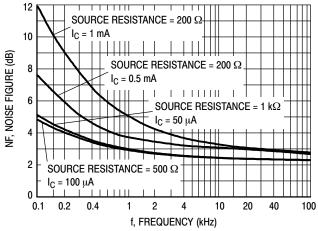


Figure 3. Frequency Variations

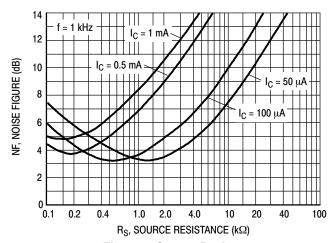


Figure 4. Source Resistance

h PARAMETERS

 $(V_{CE} = 10 \text{ V}, f = 1 \text{ kHz}, T_A = 25^{\circ}\text{C})$

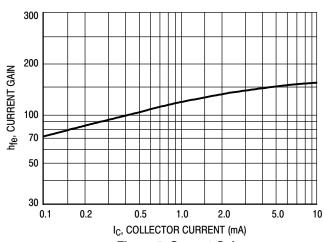


Figure 5. Current Gain

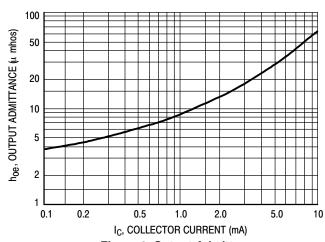


Figure 6. Output Admittance

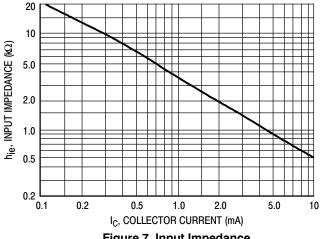


Figure 7. Input Impedance

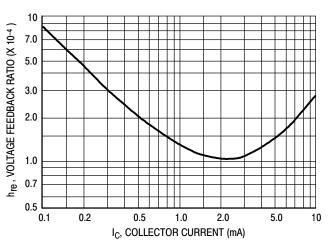


Figure 8. Voltage Feedback Ratio

STATIC CHARACTERISTICS

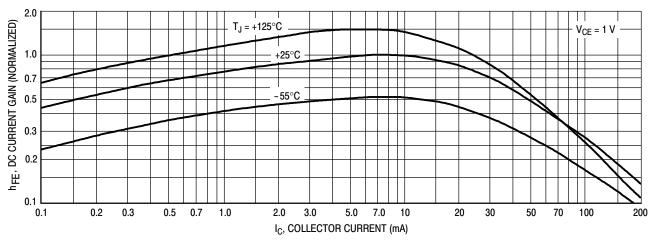


Figure 9. DC Current Gain

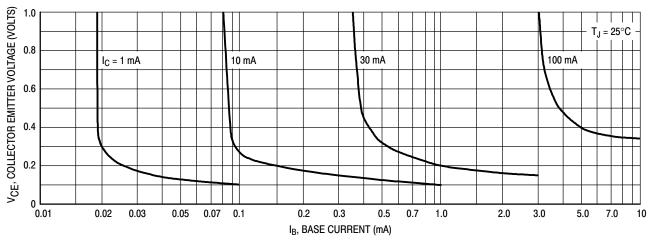


Figure 10. Collector Saturation Region

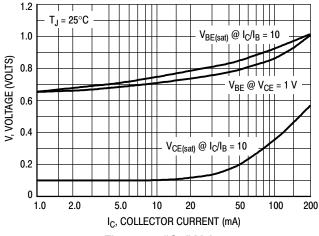


Figure 11. "On" Voltages

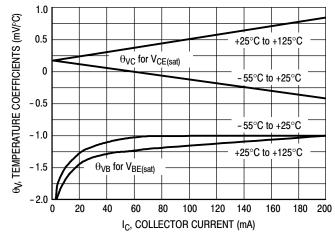
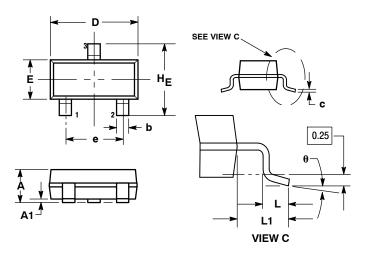


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



NOTES:

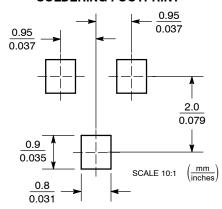
- DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES
 LEAD FINISH THICKNESS. MINIMUM LEAD
 THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 4. 318-01 THRU -07 AND -09 OBSOLETE
- NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
C	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6: PIN 1. BASE 2. EMITT

EMITTER COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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